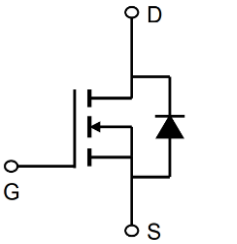
AP220N10MP

100V N-Channel Enhancement Mode MOSFET

Description

The AP220N10MP uses advanced SGTⅡ technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 10V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

V_{DS} = 100V I_D =220A

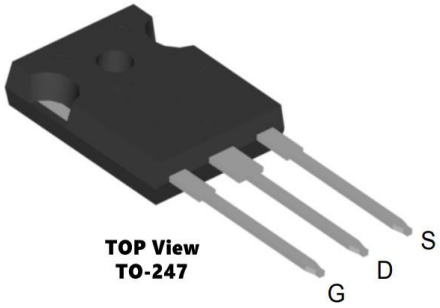
$R_{DS(ON)}$ < 2.8mΩ @ V_{GS}=10V **(Type：2.1mΩ)**

Application

DC/DC Converter

LED Backlighting

Power Management Switches



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP220N10MP	TO-247-3L	AP220N10MP XXX YYYY	1000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	220	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	180	A
IDM	Pulsed Drain Current	840	A
EAS	Single Pulse Avalanche Energy	500	mJ
IAS	Avalanche Current	106.8	A
P_D@T_C=25℃	Total Power Dissipation[4]	296	W
TSTG	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta}JA$	Thermal Resistance Junction-Ambient	0.42	℃/W
$R_{\theta}JC$	Thermal Resistance Junction-Case	40	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
VDSS	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	100	-	-	V
IGSS	Gate-body Leakage current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
IDSS	Zero Gate Voltage Drain Current T_J=25°C	V_{DS} =100V, V_{GS} = 0V	-	-	1	μA
IDSS	Zero Gate Voltage Drain Current T_J=100°C		-	-	100	
VGS(th)	Gate-Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.9	4.0	V
RDS(on)	Drain-Source on-Resistance[2]	V_{GS} = 10V, I_D = 20A	-	2.1	2.8	mΩ
Ciss	Input Capacitance	V_{DS} = 50V, V_{GS} =0V, f =1MHz	-	8800	-	pF
Coss	Output Capacitance		-	1290	-	
Crss	Reverse Transfer Capacitance		-	40	-	
R_g	Gate Resistance	V_{GS} = 0V, V_{DS} = 0V, f =1MHz	-	3.4	-	Ω
Q_g	Total Gate Charge	V_{GS} = 10V, V_{DS} = 50V, I_D=20A	-	150	-	nC
Qgs	Gate-Source Charge		-	34	-	
Qgd	Gate-Drain Charge		-	26	-	
td(on)	Turn-on Delay Time	V_{GS} =10V, V_{DS} =50V, R_G = 3Ω, I_D= 20A	-	30.8	-	ns
t_r	Rise Time		-	26	-	
td(off)	Turn-off Delay Time		-	68	-	
t_f	Fall Time		-	12.4	-	
VSD	Diode Forward Voltage[2]	I_F = 20A, V_{GS} = 0V	-	-	1.2	V
IS	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	-	-	190	A
trr	Body Diode Reverse Recovery Time	I_F = 20A, dI/dt=100A/μs	-	110	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	202	-	nC

Notes:

1、The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3、The EAS data shows Max. rating . The test condition is V_{DD}=50V, V_{GS}=10V, L=0.4mH, I_{AS}=64A

4、The power dissipation is limited by 150°C junction temperature

5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

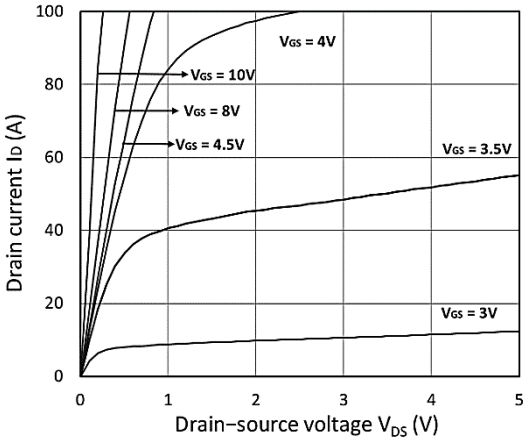


Figure 1. Output Characteristics

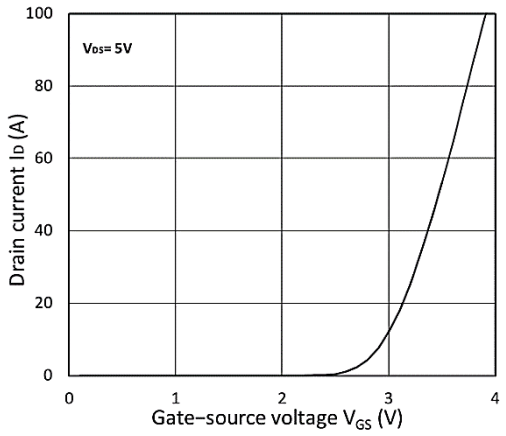


Figure 2. Transfer Characteristics

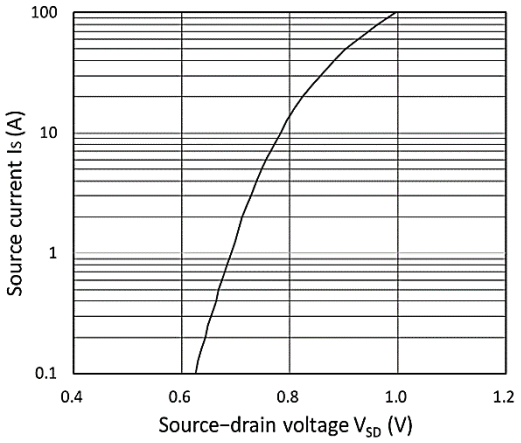


Figure 3. Forward Characteristics of Reverse

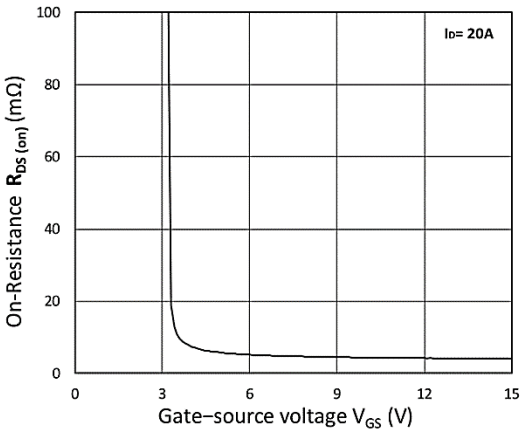


Figure 4. RDS(ON) vs. VGS

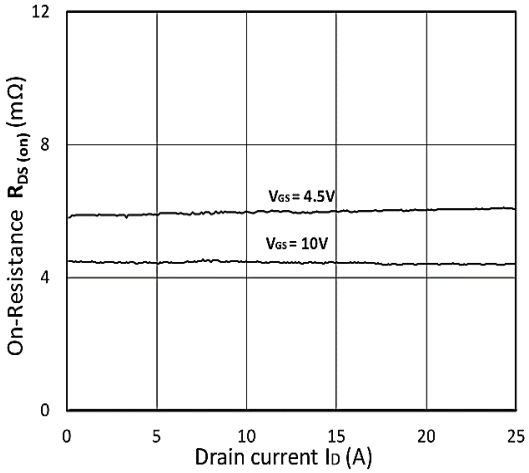


Figure 5. R DS(ON) vs. I D

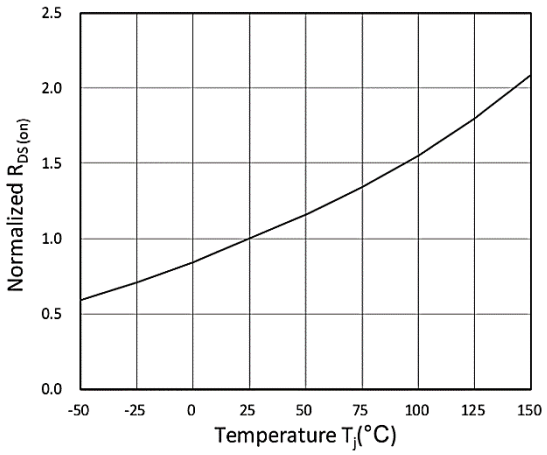


Figure 6. Normalized R DS(on) vs. Temperature

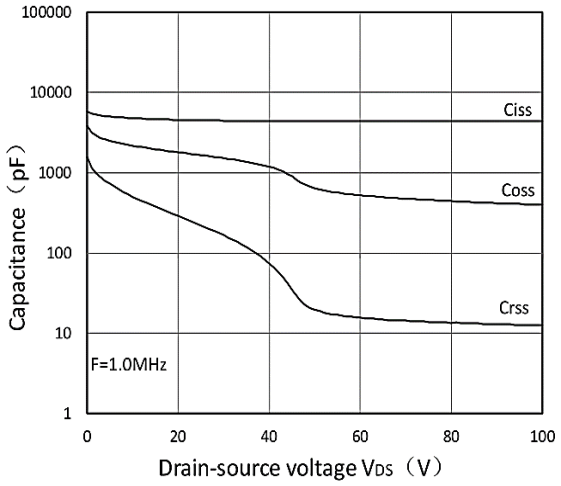


Figure 7. Capacitance Characteristics

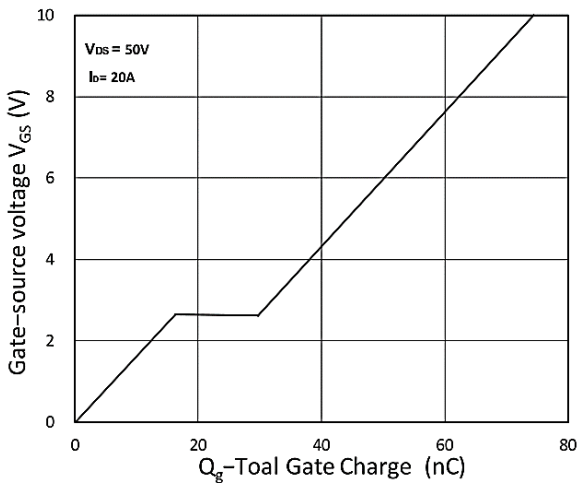


Figure 8. Gate Charge Characteristics

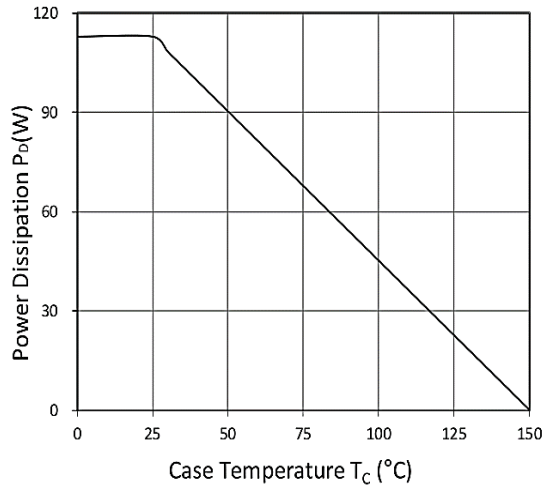


Figure 9. Power Dissipation

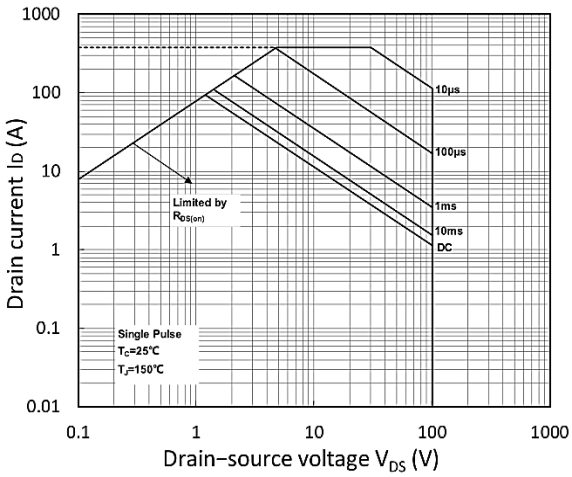


Figure10. Safe Operating Area

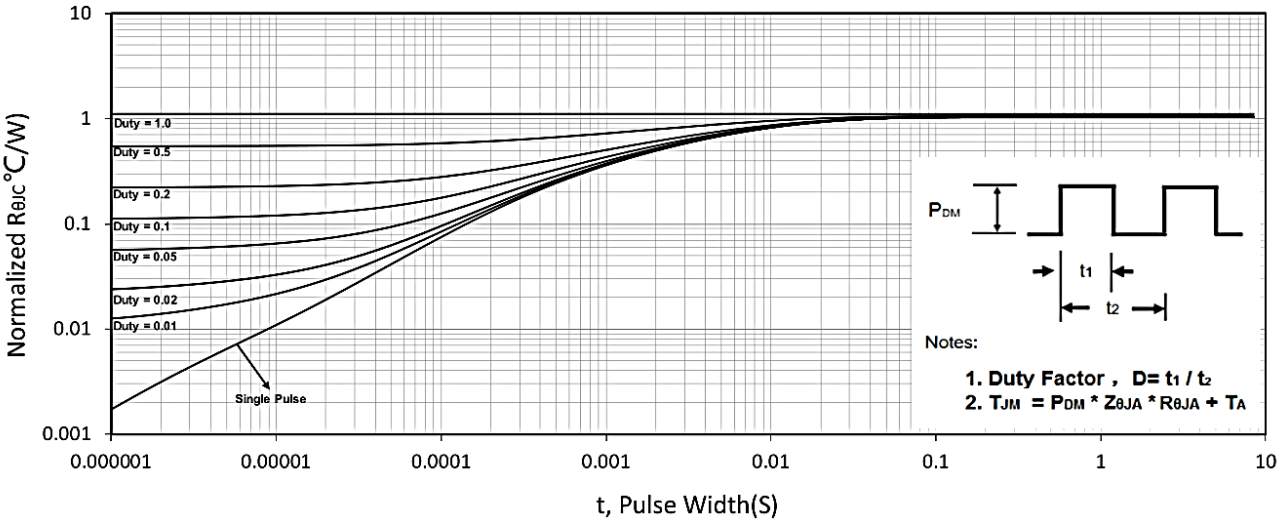
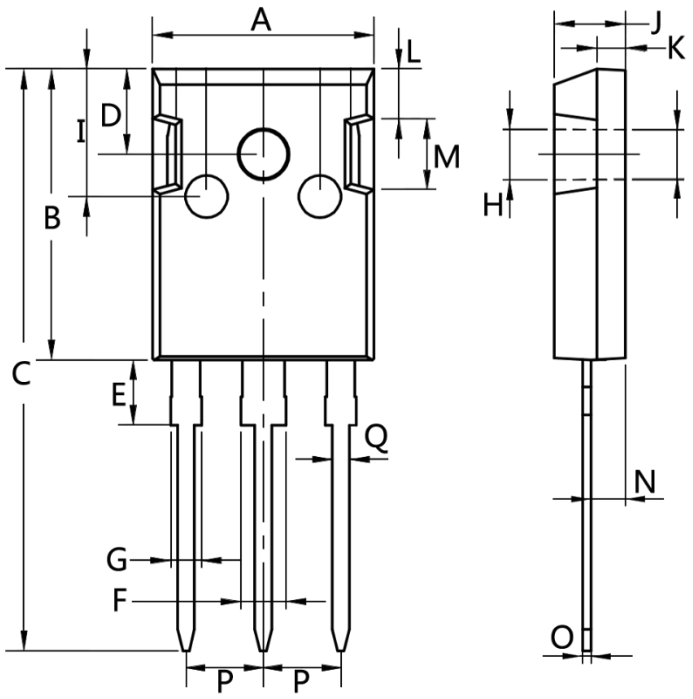


Figure 11. Normalized Maximum Transient Thermal Impedance

Package Mechanical Data-TO-247-3L



Dim.	Min.	Max.
A	15.0	16. 0
B	20.0	21.0
C	41.0	42.0
D	5.0	6.0
E	4.0	5.0
F	2.5	3.5
G	1.75	2.5
H	3.0	3.5
I	8.0	10.0
J	4.9	5.1
K	1.9	2.1
L	3.5	4.0
M	4.75	5.25
N	2.0	3.0
O	0.55	0.75
P	Typ 5.08	
Q	1.2	1.3